



# PWRLITE LVTD103N

## High Performance N-Ch Vertical Power JFET Transistor “No Diode”

### Features

- ❖ Trench Power JFET with low threshold voltage  $V_{th}$ .
- ❖ Device fully “ON” with  $V_{gs} = 0.7V$
- ❖ Optimum for “Low Side” Buck Converters
- ❖ Optimized for Secondary Rectification in isolated DC-DC Converters
- ❖ Low  $R_g$  and low  $C_{ds}$  for high speed switching
- ❖ No “Body Diode”; extremely low  $C_{ds}$

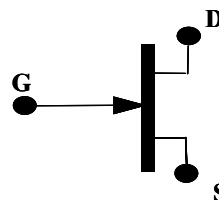
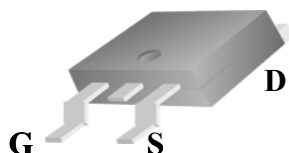
### Applications

- ❖ DC-DC Converters
- ❖ Synchronous Rectifiers
- ❖ PC Motherboard Converters
- ❖ Step-down power supplies
- ❖ Brick Modules
- ❖ VRM Modules

### Description

The Power JFET transistor from Lovoltech is a device that presents a Low  $R_{ds(on)}$  allowing for improved efficiencies in DC-DC switching applications. The device is designed with a low threshold such that drivers can operate at 5V, which reduces the driver power dissipation and increases the overall efficiency. Lower threshold produces faster turn-on/turn-off, which minimizes the required dead time. The transistor “No Body Diode” provides a very low associated parasitic capacitance  $C_{ds}$ . Ringing is also reduced so that a lower voltage device may be a better solution.

### DPAK Pin Assignments



N – Channel Power JFET

### Pin Definitions

| Pin Number | Pin Name | Pin Function Description         | Product Summary |                           |           |
|------------|----------|----------------------------------|-----------------|---------------------------|-----------|
|            |          |                                  | $V_{DS}$ (V)    | $R_{ds(on)}$ ( $\Omega$ ) | $I_D$ (A) |
| 1          | Gate     | <b>Gate.</b> Transistor Gate     | 25V             | 0.005 @ $I_g = 10mA$      | 50        |
| 2          | Drain    | <b>Drain.</b> Transistor Drain   | 25V             | 0.0045 @ $I_g = 40mA$     | 50        |
| 3          | Source   | <b>Source.</b> Transistor Source |                 |                           |           |

### Absolute Maximum Ratings

| Parameter                              | Symbol   | Ratings               | Units        |
|--|----------|-----------------------|--------------|
| Drain-Source Voltage                   | $V_{DS}$ | 25 (selection @ 30V)  | V            |
| Gate-Source Voltage                    | $V_{GS}$ | -10                   | V            |
| Gate-Drain Voltage                     | $V_{GD}$ | -25(selection @ -30V) | V            |
| Continuous Drain Current               | $I_D$    | 50                    | A            |
| Pulsed Drain Current                   | $I_D$    |                       | A            |
| Junction Temperature                   | $T_J$    | -55 to 150°C          | °C           |
| Storage Temperature                    |          | -65 to 150°C          | -65 to 150°C |
| Lead Soldering Temperature, 10 seconds | 300°C    | 300°C                 | 300°C        |
| Power Dissipation (derated at 25°C)    | $P_D$    | 80                    | W            |

## Thermal Resistance

| Symbol         | Parameter                              |  | DPAK Ratings |  | Units |
|----------------|--|--|--------------|--|-------|
| $R\Theta_{JA}$ | Thermal Resistance Junction-to-Ambient |  | 80           |  | °C/W  |
| $R\Theta_{JC}$ | Thermal Resistance Junction-to-Case    |  | 1.6          |  | °C/W  |

## Electrical Specifications

( $T_A = +25^\circ\text{C}$ , unless otherwise noted.)

The  $\phi$  denotes specifications which apply over the full operating temperature range.

| Symbol         | Parameter  | Conditions   |        | Min. | Typ.       | Max.     | Units                               |
|----------------|--|--|--------|------|------------|----------|-------------------------------------|
| <b>Static</b>  |  |  |        |      |            |          |                                     |
| $BV_{DSX}$     | Breakdown Voltage Drain to Source  | See Figure 3   | $\phi$ |      | 25         |          | V                                   |
| $BV_{GDO}$     | Breakdown Voltage Gate to Drain  | $I_G = -50\mu\text{A}$   | $\phi$ |      | -25        |          | V                                   |
| $BV_{GSO}$     | Breakdown Voltage Gate to Source   | $I_G = -1\text{ mA}$   | $\phi$ |      | -11        | -10      | V                                   |
| $R_{DS(ON)}$   | Static Drain to Source <sup>1</sup> On Resistance (Current flows drain-to-source) See Fig. 1 | $I_G = 40\text{ mA}$ , $I_D = 10\text{A}$<br>$I_G = 10\text{ mA}$ , $I_D = 10\text{A}$           |        |      | 4.5<br>5.0 | 5.5<br>6 | $m\Omega$<br>$m\Omega$<br>$m\Omega$ |
| $V_{GS(TH)}$   | Gate Threshold Voltage   | $V_{DS} = 0.1\text{ V}$ , $I_D = 250\mu\text{A}$   | $\phi$ | -0.4 | -0.3       | -0.2     | V                                   |
| <b>Dynamic</b> |  |  |        |      |            |          |                                     |
| $Q_G$          | Total Gate Charge  | $\Delta V_{Drive} = 5\text{V}$ , $I_D = 15\text{A}$ , $V_{DS} = 16\text{V}$                      |        |      | 20         |          | nC                                  |
| $Q_{GD}$       | Gate to Drain Charge   |  |        |      | 12         |          | nC                                  |
| $Q_{GS}$       | Gate to Source Charge  |  |        |      | 1.5        |          | nC                                  |
| $Q_{SW}$       | Switching Charge   |  |        |      | 13.5       |          | nC                                  |
| $R_G$          | Gate Resistance  |  |        |      | 0.3        |          | $\Omega$                            |
| $T_{D(ON)}$    | Turn-on Delay Time   | $V_{DD} = 16\text{V}$ , $I_D = 15\text{A}$<br>$V_{Drive} = 5\text{ V}$<br>Clamped Inductive Load | $\phi$ |      | 5          |          | ns                                  |
| $T_R$          | Rise Time  |  | $\phi$ |      | 12         |          |                                     |
| $T_{D(OFF)}$   | Turn-off Delay   |  |        |      | 2          |          |                                     |
| $T_F$          | Fall Time  |  |        |      | 10         |          |                                     |
| $C_{ISS}$      | Input Capacitance  | $V_{DS} = 10\text{V}$ , $V_{GS} = -5\text{ V}$ , 1MHz.   |        |      | 3000       |          | pF                                  |
| $C_{OSS}$      | Output Capacitance   |  |        |      | 760        |          |                                     |
| $C_{GS}$       | Gate-Source Capacitance  |  |        |      | 2250       |          |                                     |
| $C_{GD}$       | Gate-Drain Capacitance   |  |        |      | 750        |          |                                     |
| $C_{DS}$       | Drain-Source Capacitance   |  |        |      | 10         |          |                                     |
|                |  |  |        |      |            |          |                                     |

### Notes:

1. Pulse width  $\leq 500\mu\text{s}$ , duty cycle  $\leq 2\%$

## Typical Operating Characteristics

( $T_A = +25^\circ\text{C}$ , unless otherwise noted.)

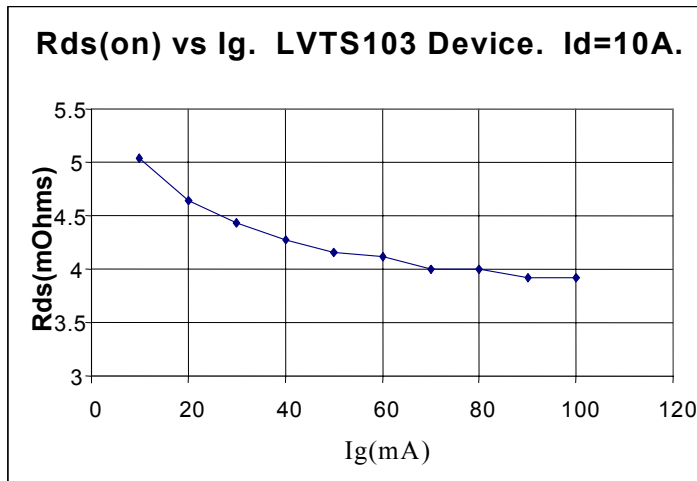


Figure 1 –  $R_{DS(on)}$  vs Gate Current at  $I_D = 10\text{A}$

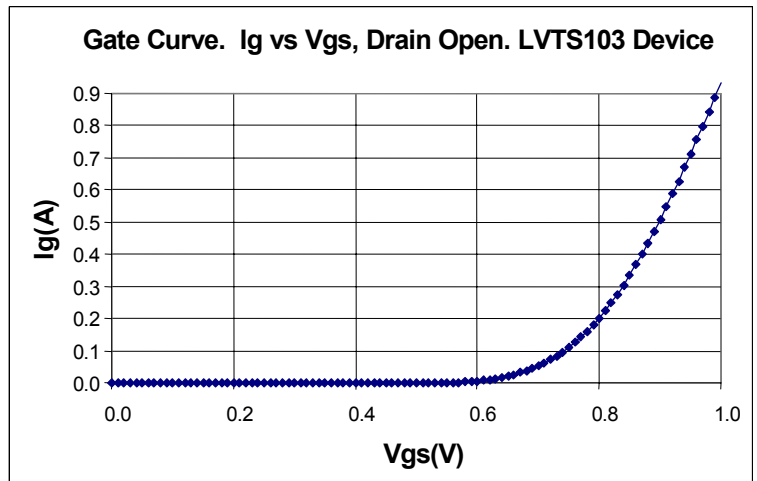


Figure 2 –  $I_G$  vs Gate Voltage  $V_{GS}$

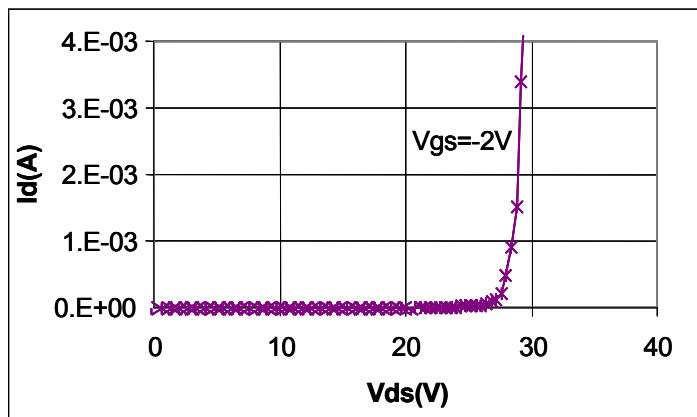


Figure 3 – Breakdown Voltage  $V_{ds}$

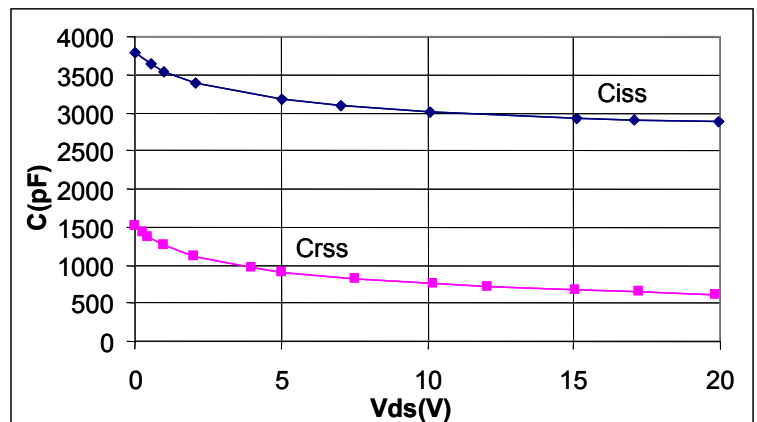


Figure 4 – Capacitance vs Drain Voltage  $V_{ds}$

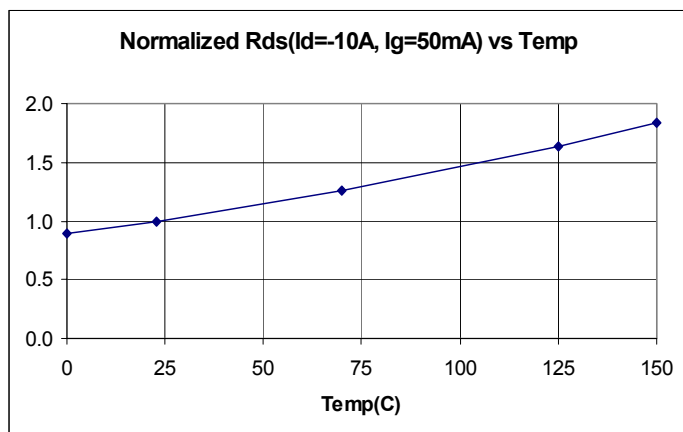


Figure 5 – Normalized On-Resistance vs. Temperature

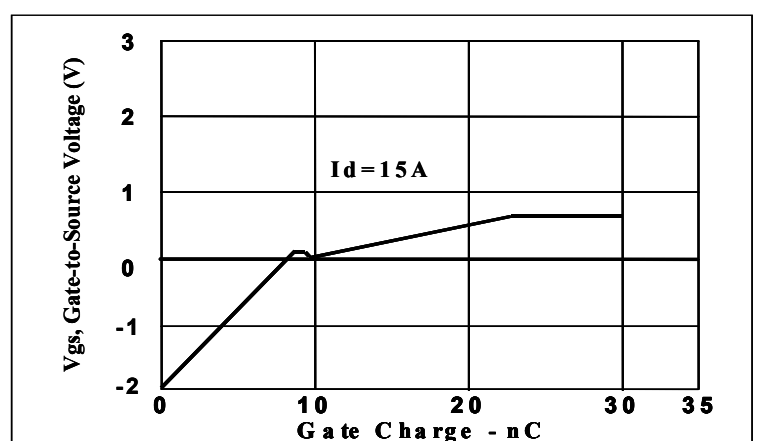


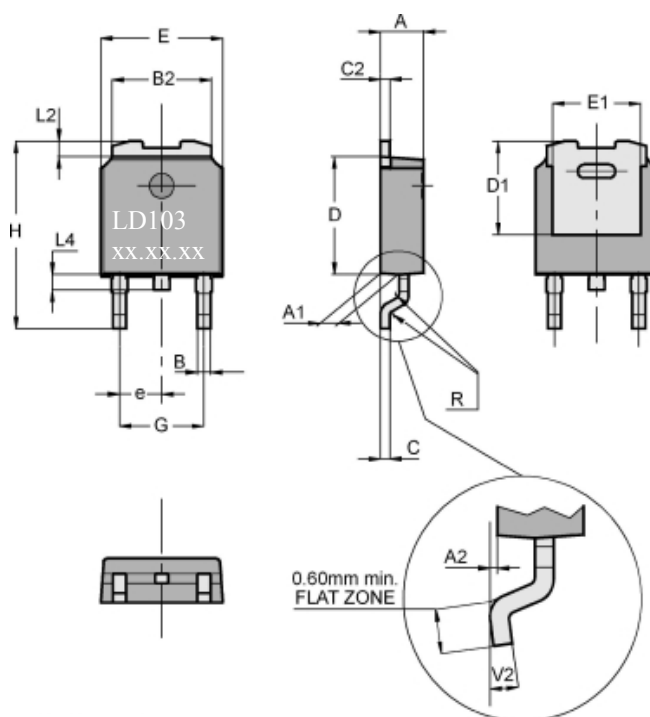
Figure 6 – Typical Gate Charge vs. Gate-to-Source Voltage

## Ordering Information

| Product Number           | PN Marking                | Package      |
|--------------------------|---------------------------|--------------|
| LD103Nx<br>x= 0, 2, 5, 6 | LD103Nx<br>x = Lot Source | TO252 (DPAK) |

## Package and Marking Information

| DPAK DIMENSIONS |      |      |       |       |       |       |
|-----------------|------|------|-------|-------|-------|-------|
| DIM.            | mm.  |      |       | inch  |       |       |
|                 | TYP. | MIN. | MAX.  | TYP.  | MIN.  | MAX.  |
| A               |      | 2.20 | 2.40  |       | 0.086 | 0.094 |
| A1              |      | 0.90 | 1.10  |       | 0.035 | 0.043 |
| A2              |      | 0.03 | 0.23  |       | 0.001 | 0.009 |
| B               |      | 0.64 | 0.90  |       | 0.025 | 0.035 |
| B2              |      | 5.20 | 5.40  |       | 0.204 | 0.212 |
| C               |      | 0.45 | 0.60  |       | 0.017 | 0.023 |
| C2              |      | 0.48 | 0.60  |       | 0.019 | 0.023 |
| D               |      | 6.00 | 6.20  |       | 0.236 | 0.244 |
| D1              | 5.10 |      |       | 0.201 |       |       |
| E               |      | 6.40 | 6.60  |       | 0.252 | 0.260 |
| E1              | 4.70 |      |       | 0.185 |       |       |
| e               | 2.28 |      |       | 0.090 |       |       |
| G               |      | 4.40 | 4.60  |       | 0.173 | 0.181 |
| H               |      | 9.35 | 10.10 |       | 0.368 | 0.397 |
| L2              | 0.80 |      |       | 0.031 |       |       |
| L4              |      | 0.60 | 1.00  |       | 0.023 | 0.039 |
| R               | 0.20 |      |       | 0.008 |       |       |
| V2              |      | 0°   | 8°    |       | 0°    | 8°    |



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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

| Datasheet Identification | Product Status             | Definition   |
|--------------------------|----------------------------|--|
| Advance Information      | In definition or in Design | This datasheet contains the design specifications for product development. Specifications may change without notice.   |
| Preliminary              | Initial Production         | This datasheet contains preliminary data; additional and application data will be published at a later date. Lovoltech, Inc. reserves the right to make changes at any time without notice in order to improve design. |
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